



### 100V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max Tc = +25°C		
100V	32mΩ @ V <sub>GS</sub> = 10V	35A		

### **Description**

This MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

## **Applications**

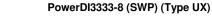
- Backlighting
- Power Management Functions
- DC-DC Converters

### **Features and Benefits**

- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Wettable Flank for Improved Optical Inspection
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

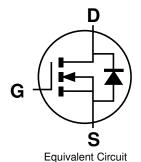
### **Mechanical Data**

- Case: PowerDI<sup>®</sup>3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 (§3)
- Weight: 0.072 grams (Approximate)









### Ordering Information (Note 4)

Part Number	Case	Packaging
DMT10H032SFVW-7	PowerDI3333-8 (SWP) (Type UX)	2,000/Tape & Reel
DMT10H032SFVW-13	PowerDI3333-8 (SWP) (Type UX)	3,000/Tape & Reel

Notes: 1.

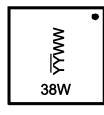
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

**Bottom View** 

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# **Marking Information**

### PowerDI3333-8 (SWP) (Type UX)



38W = Product Type Marking Code

YYWW = Date Code Marking

YY = Last Two Digits of Year (ex: 20 = 2020)

WW = Week Code (01 to 53)



# **Maximum Ratings** (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V <sub>DSS</sub>	100	V	
Gate-Source Voltage	Vgss	±20	V	
	Tc = +25°C		35	Α
Continuous Drain Current (Note 7) VGS = 10V	Tc = +70°C	ID	28	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	Ірм	140	Α	
Maximum Continuous Body Diode Forward Current (Note 7)	Is	26	Α	
Pulsed Body Diode Forward Current (Note 8)	I <sub>SM</sub>	140	Α	
Avalanche Current, L = 0.3mH (Note 8)	las	13	Α	
Avalanche Energy, L = 0.3mH (Note 8)	E <sub>AS</sub>	25.35	mJ	

# Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

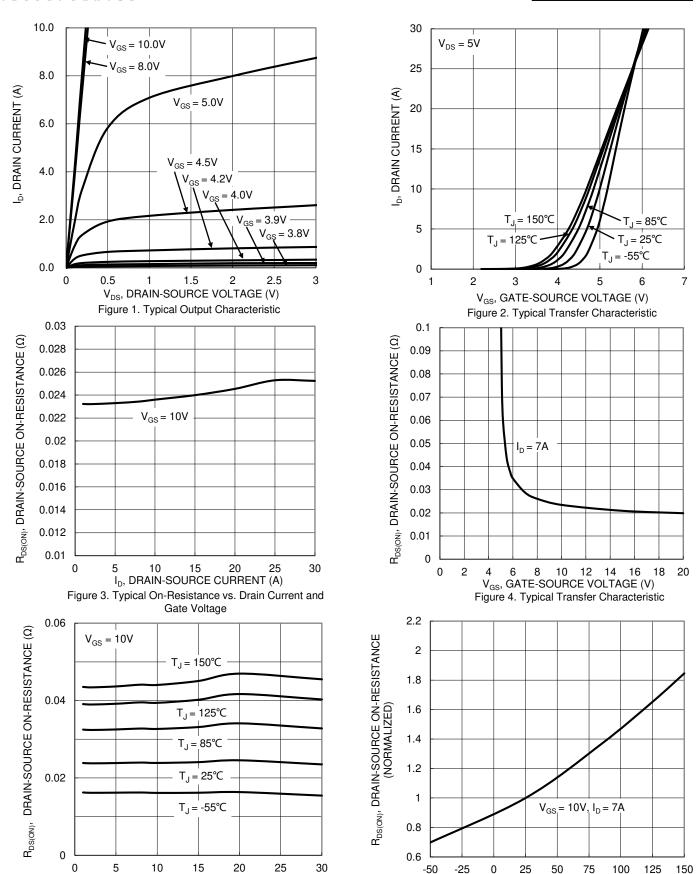
Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	PD	1.3	W	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	97	°C/W
Total Power Dissipation (Note 6)	PD	2.5	W	
Thermal Resistance, Junction to Ambient (Note 6)  Steady State		$R_{\theta JA}$	50	°C/W
Thermal Resistance, Junction to Case (Note 7)	Rejc	2.1	C/VV	
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BVDSS	100	_	_	V	$V_{GS} = 0V$ , $I_D = 1mA$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 80V, V_{GS} = 0V$	
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	2	_	4	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>		24	32	mΩ	$V_{GS} = 10V$ , $I_D = 7A$	
Diode Forward Voltage	V <sub>SD</sub>	_	0.86	1	V	$V_{GS} = 0V, I_{S} = 7A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	Ciss	_	544	_	pF	., 50,4,74	
Output Capacitance	Coss	_	181	_	рF	V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V, f = 1MHz	
Reverse Transfer Capacitance	Crss	_	6.0	_	pF		
Gate Resistance	Rg	_	1.2	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (VGS = 4.5V)	Qg	_	4.3	_	nC		
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	8.0	_	nC	\/aa	
Gate-Source Charge	Qgs	_	1.8	_	nC	$V_{DS} = 50V$ , $I_{D} = 7A$	
Gate-Drain Charge	$Q_{gd}$	_	2.4	_	nC	7	
Turn-On Delay Time	tD(ON)	_	8.5	_	ns		
Turn-On Rise Time	tr	_	2.7	_	ns	V <sub>DS</sub> = 50V, I <sub>D</sub> = 7A	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	11.9	_	ns	$V_{GS} = 10V$ , $R_{GEN} = 6\Omega$	
Turn-Off Fall Time	tF	_	6.2	_	ns		
Reverse Recovery Time	trr	_	33.2	_	ns	I <sub>F</sub> = 7A, di/dt = 100A/μs	
Reverse Recovery Charge	Qrr	_	34.3	_	nC		

- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
- 7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
   Short duration pulse test used to minimize self-heating effect.
   Guaranteed by design. Not subject to product testing.





I<sub>D</sub>, DRAIN CURRENT (A)

Figure 5. Typical On-Resistance vs. Drain Current and

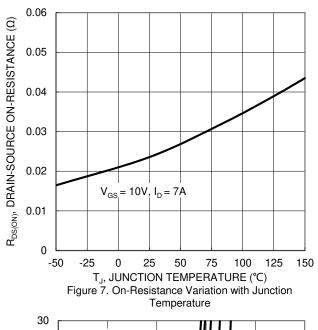
Junction Temperature

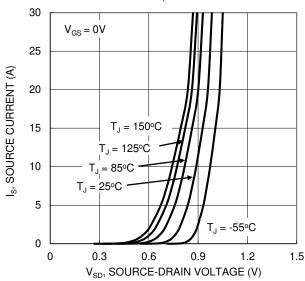
T<sub>.</sub>, JUNCTION TEMPERATURE (°C)

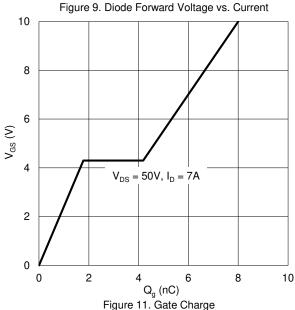
Figure 6. On-Resistance Variation with Temperature











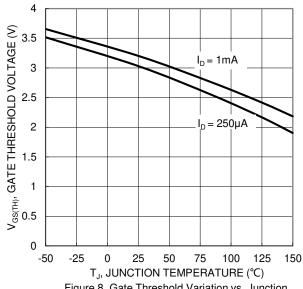
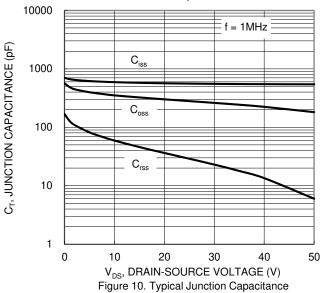


Figure 8. Gate Threshold Variation vs. Junction Temperature



1000  $\begin{array}{c} R_{\text{DS(ON)}} \\ \text{Limited} \end{array}$ 100 ID, DRAIN CURRENT (A) 10 P<sub>W</sub> = 10μs P<sub>W</sub> = 100μs 1  $T_{J(Max)}=150\,{}^{\circ}\mathrm{C}$  $T_C = 25^{\circ}C$ Single Pulse DUT on Infinite Heatsink  $V_{GS} = 10V$ 0.01 100 0.1 10 1000  $V_{DS}$ , DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area



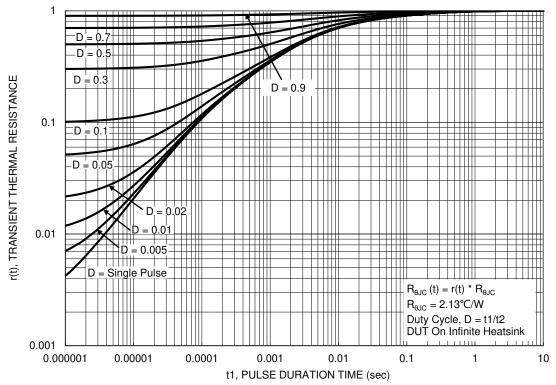


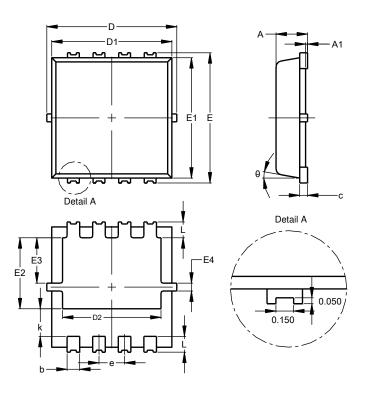
Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### PowerDI3333-8 (SWP) (Type UX)

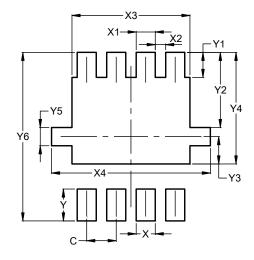


PowerDI3333-8 (SWP)						
(Type UX)						
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
<b>A</b> 1	0.00	0.05				
b	0.25	0.40	0.32			
С	0.10	0.25	0.15			
D	3.20	3.40	3.30			
D1	2.95	3.15	3.05			
D2	2.30	2.70	2.50			
Ε	3.20	3.40	3.30			
E1	2.95	3.15	3.05			
E2	1.60	2.00	1.80			
E3	0.95	1.35	1.15			
E4	0.10	0.30	0.20			
е			0.65			
k	0.50	0.90	0.70			
L	0.30	0.50	0.40			
θ	0°	12°	10°			
All Dimensions in mm						

# Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

### PowerDI3333-8 (SWP) (Type UX)



Dimensions	Value (in mm)			
С	0.650			
Х	0.420			
X1	0.420			
X2	0.230			
Х3	2.600			
X4	3.500			
Υ	0.700			
Y1	0.550			
Y2	1.650			
Y3	0.600			
Y4	2.450			
Y5	0.400			
Y6	3.700			



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